**CLAIM AMENDMENTS:**

Claim 1 (Original): A combined semiconductor apparatus comprising:

a semiconductor substrate having an integrated circuit;

a planarized region formed in a surface of said semiconductor substrate; and

a semiconductor thin film including at least one semiconductor device and bonded on said planarized region.

Claim 2 (Original): The combined semiconductor apparatus according to claim 1, wherein said planarized region is a part of said surface of said semiconductor substrate which has been subjected to a planarizing process.

Claim 3 (Original): The combined semiconductor apparatus according to claim 1, wherein said planarized region is disposed above said integrated circuit of said semiconductor substrate.

Claim 4 (Original): The combined semiconductor apparatus according to claim 1, wherein said planarized region is disposed in a region of said semiconductor substrate adjacent to said integrated circuit of said semiconductor substrate.

Claim 5 (Original): The combined semiconductor apparatus according to claim 1, further comprising a planarized film disposed between said planarized region and said semiconductor thin film, wherein a surface of said planarized film on a side of said semiconductor thin film has been subjected to a planarizing process.

Claim 6 (Original): The combined semiconductor apparatus according to claim 5, wherein said planarized film includes:

an electrically conductive layer; and

an interdielectric layer formed in a region peripheral to said electrically conductive layer.

Claims 7 and 8 (Canceled).

Claim 9 (Original): The combined semiconductor apparatus according to claim 1, wherein said semiconductor thin film has a common electrode layer on a second surface of the semiconductor thin film opposed to a first surface of the semiconductor thin film, in which said semiconductor device is formed, and

said second surface of said semiconductor thin film is disposed on a side of said planarized region of said semiconductor substrate.

Claim 10 (Original): The combined semiconductor apparatus according to claim 9, wherein said integrated circuit includes individual electrode terminals;

said apparatus further comprising individual interconnecting lines formed on a region extending from an upper surface of said semiconductor device to said individual electrode terminal.

Claims 11- 15 (Canceled).

Claim 16 (Original): The combined semiconductor apparatus according to claim 1, wherein said semiconductor thin film is made of compound semiconductor as a main materials.

Claim 17 (Original): The combined semiconductor apparatus according to claim 1, wherein said at least one semiconductor device is any of a light-emitting element, a light-sensing element, a Hall element and a piezoelectric element, and said integrated circuit includes a driving-IC for driving said at least one semiconductor device.

Claim 18 (Original): The combined semiconductor apparatus according to claim 1, wherein said at least one semiconductor device is a plurality of said semiconductor devices arranged in said semiconductor thin film.

Claim 19 (Original): The combined semiconductor apparatus according to claim 1, wherein said at least one semiconductor device is a single semiconductor device disposed in said semiconductor thin film.

Claim 20 (Original): An optical print head including the combined semiconductor apparatus of claim 1.

Claims 21-25 (Canceled).

Claim 26 (New): A combined semiconductor apparatus according to claim 1, further comprising:

an integrated circuit device disposed on said semiconductor substrate;

a raised layer formed on a surface of said semiconductor substrate in a region adjacent to said integrated circuit device, an upper surface of said raised layer being at a position higher than an upper surface of said integrated circuit device; and

another semiconductor thin film bonded on the upper surface of said raised layer.

Claim 27 (New): An optical print head including the combined semiconductor apparatus of claim 26.

Claim 28 (New): An image-forming apparatus comprising at least one optical print head including the combined semiconductor apparatus of claim 26.

Claim 29 (New): A combined semiconductor apparatus according to claim 1, wherein a first surface of said semiconductor thin film, in which said semiconductor device is formed, is disposed on a side of said semiconductor substrate.

Claim 30 (New): The combined semiconductor apparatus according to claims 29, further comprising an electrically conductive layer disposed between said semiconductor substrate and said semiconductor thin film.

Claim 31 (New): The combined semiconductor apparatus according to claim 29, further comprising an interdielectric layer disposed between said semiconductor substrate and said semiconductor thin film and in a region peripheral to said electrically conductive layer.

Claim 32 (New): The combined semiconductor apparatus according to claim 29, wherein said semiconductor thin film includes a common electrode layer on a second surface of said semiconductor thin film opposed to said first surface, and said integrated circuit has a common electrode terminal;

said apparatus further comprising a common interconnecting layer

formed on a region extending from an upper surface of said common electrode layer of said semiconductor thin film to said common electrode terminal of said integrated circuit.

Claim 33 (New): An optical print head including the combined semiconductor apparatus of claim 29.

Claim 34 (New): An image-forming apparatus comprising at least one optical print head including the combined semiconductor apparatus of claim 29.